

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0005] with the following amended paragraph:

[0005] The present invention relates to a method of forming a conductive pattern of a semiconductor device, and to a method of manufacturing a non-volatile semiconductor memory device using the conductive pattern. ~~conductive pattern~~

Please replace paragraph [0145] with the following amended paragraph:

[0145] Finally, a conductive pattern having good uniformity is formed on the semiconductor substrate by polishing the step compensation layer, the polishing protection layer and the conductive layer (step S14). In particular, the conductive pattern is formed by a primary planarization process and a secondary planarization ~~process~~ ~~process~~ generate.